TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington Power Transistor)

2SD2385

Power Amplifier Applications

- High breakdown voltage: VCEO = 140 V (min)
- Complementary to 2SB1556

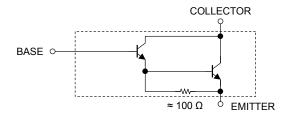
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	140	V
Collector-emitter voltage	V _{CEO}	140	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	8	А
Base current	Ι _Β	0.1	А
Collector power dissipation (Tc = 25°C)	Pc	120	W
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55 to 150	°C

20.5MAX Ø3.3±0.2 26.0±0 0.1 2.0 .50 20.0±0.6 +0.3 1.0-0.2 5<u>.45 ± 0.15</u> 5.45 ± 0.15 +0.25 2 3 BASE 1. 2. COLLECTOR (HEAT SINK) 3. EMITTER JEDEC ____ JEITA _ TOSHIBA 2-21F1A

Weight: 9.75 g (typ.)

Equivalent Circuit



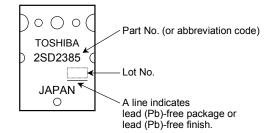
Unit: mm

Electrical Characteristics (Ta = 25°C)

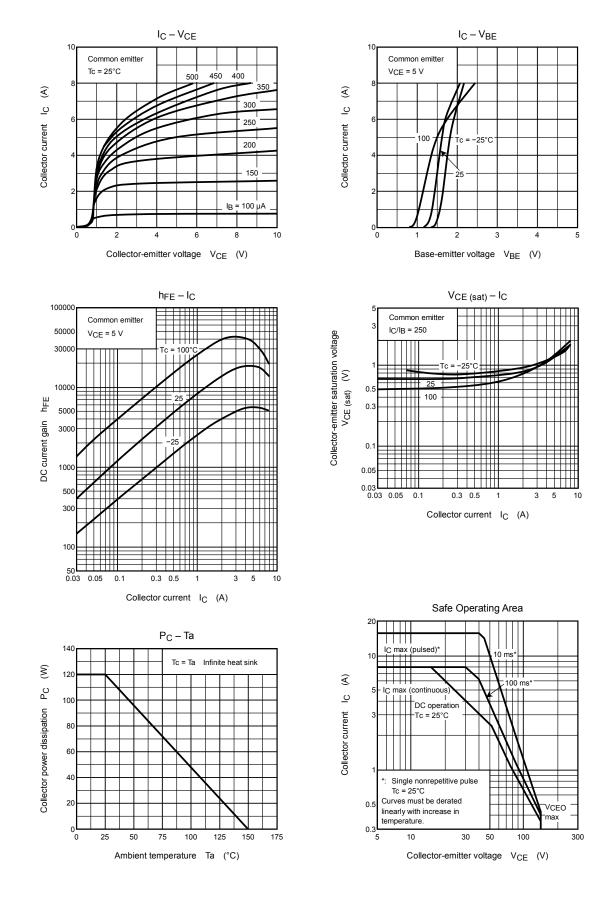
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 140 V, I _E = 0	_	_	5.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	5.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	140	_	_	V
DC current gain	h _{FE (1)} (Note)	V _{CE} = 5 V, I _C = 7 A	5000	_	30000	_
	h _{FE (2)}	V _{CE} = 5 V, I _C = 12 A	2000	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 7 A, I _B = 7 mA	_	_	2.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 7 A	_	_	3.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 1 A	_	30	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	—	110	—	pF

Note: hFE (1) classification A: 5000 to 12000, B: 9000 to 18000, C: 15000 to 30000

Marking



TOSHIBA



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